

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS L1	847	(heat\$3 WITH crystalliz?\$2) AND ((irradiat?\$2 laser) WITH (crystal crystalli?\$2)) ((CRYSTALLIZ?\$2 WITH HEAT\$3) AND ((CRYSTALLI?\$2 OR CRYSTAL) WITH (anneal\$3)))	USPAT; EPO; JPO; Derwent	2000/04/17 12:22		0	
2	BRS L2	733		USPAT; EPO; JPO; Derwent	2000/04/17 12:23		0	
3	BRS L3	1282	1 2	USPAT; EPO; JPO; Derwent	2000/04/17 12:23		0	
4	BRS L4	617	3 AND (insulating dielectric oxide nitride) ADJ2 (layer film substrate)	USPAT; EPO; JPO; Derwent	2000/04/17 12:26		0	
5	BRS L5	457	4 AND ((semiconductor silicon "gallium arsenide" GaAs) ADJ2 (FILM OR LAYER))	USPAT; EPO; JPO; Derwent	2000/04/17 12:28		0	
6	BRS L6	40	5 AND (mov?\$2 WITH laser)	USPAT; EPO; JPO; Derwent	2000/04/17 12:29		0	
7	BRS L7	27	6 AND (laser WITH (rectangular section elongated))	USPAT; EPO; JPO; Derwent	2000/04/17 12:37		0	
8	BRS L8	15	7 AND @ad<19960718	USPAT; EPO; JPO; Derwent	2000/04/17 12:40		0	
9	BRS L9	7	(8 AND (@AD < "19950719"))	USPAT; EPO; JPO; Derwent	2000/04/17 12:58		0	
10	BRS L10	8	8 NOT 9	USPAT; EPO; JPO; Derwent	2000/04/17 12:58		0	

EST reh

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